

CIA-RDP86-00513R001652510011-9 'APPROVED FOR RELEASE: 08/23/2000

Sorohin, U.V.

TITLE: .

137-1957-12-25416

Translation from: Referativnyy zhurnal, Metallurgiya, 1957, Nr 12, p 351 (USSR)

Sorokin, O. V., Tulyakov, G. A.

AUTHORS:

An Installation for Creep-Testing of Metals Under Combined Stresses (Tension With Torsion) [Ustanovka dlya ispytaniya metallov na polzuchest' pri slozhno-napryazhennom sostovanii

(rastyazheniye s krucheniyem)

PERIODICAL: V sb.: Prochnost' metallov. Moscow, 1956, pp 50-54

A critical survey of a series of methods and various equipment for creep-testing of metals under various load conditions. Creep ABSTRACT: studies of metals exposed to combined stresses under action of tension and torsion, were carried out on a re-designed testing machine of the IP-2 type. Maximal load on the specimen comprised a 3000-kg tension and a 15-kgm torsion. The design of

the machine permits the testing of three types of stress conditions: Pure tension, pure torsion, and a combination of tension and torsion. Specimens being tested on the machine are hollow cylinders with diameters of 25 mm and 22 mm and a length of 100 mm. Torque (T) is transmitted to the specimen by means of a disc of

constant radius, secured to the upper gripping assembly by means Card 1/2

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An Installation for Creep-Testing of Metals Under Combined Stresses

of a key. The turning effort is transmitted to the disc by means of thin wire cables, which pass over pulleys mounted on the housing of the machine. In order to prevent skewing when T is applied, the lower assembly is equipped with an additional, spherical bearing. Axial and angular deformations are registered on a specially designed extensometer, employing micrometer indicators (two of which record tension, while the third registers torsion), with graduations of 0.002 mm each. In order to prevent torsional forces from affecting the readings of the tension indicators, and vice versa, the supporting plates may be regulated by means of adjusting screws. The modified machine operated quite satisfactorily during long periods of creep testing at elevated temperatures.

1. Metals-Creep-Testing equipment 2. Metals-Creep-Test methods

Card 2/2

SOROKINO. V.
USSR/Electricity - Semiconductors

G-3

Abs Jour

: Referat Zhur - Fizika, No 5, 1957, 12190

Author

: Kaganer, V.E., Regel', A.R., Sorokin, O.V.

Inst

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Title

Effect of Ion Bombardment on the Detecting Properties of

Semiconductors.

Orig Pub

: Sb. statey Leningr. in ta tochnoy mekhan. i optiki, 1955,

vyp. 18, 126-141

Abstract

An investigation was made of the influence of ion bombard-ment (IB) on the voltage-current characteristics of a point contact Si, Ge, SiC, PbS, and SbZn with tungsten. The ion bombardment was carried out with ions of hydrogen, air, oxygen, benzine, tellurium, and manganese, in order to obtain p-n and p-n-p junctions on the surface of the crystals. The effect of ion bombardment on the rectifying properties of the crystals was established as a function of the initial treatment of the semiconductor, of the

Card 1/3

most strongly, when the bombarding ion is capable of entering into a chemical bond with the element that forms the semiconductor or else with its surface layer. The most

APPROVED TERM RELITABLE 0892392000 bembardment annears with semiconductors having the purest composition. By Means of ion bombardment it is possible to produce between surfaces contact that normally are difficult to produce by other means. Ion bombardment can improve and worsen the rectifying properties of a semiconductor and are not a guaranteed universal means of obtaining good detectors, as was stated by Russel (Russel, S., Bell System Technical Journal, January 1952). In many cases the ion bombardment in itself or in combination with other types of surface treatment makes it possible to obtain good detectors. The best

Card 2/3

USSR/Electricity - Semiconductors

G-3

Abs Jour

: Ref Zhur - Fizika, No 5, 1957, 12190

detector obtained by means of ion bombardment was with n- and p-SiG. Bombardment of n-germanium by ions of air, hydrogen, or benzine vapors with subsequent polishing and etching for ten minutes in 3% solution of H₂O₂, increases substantially the rectification coefficient and the inverse voltage (to 100 volts). In all cases, ion bombardment of crystals has led to a change in the form of the voltage-current characteristics, without improving the rectifying properties of the specimens.

SOROKIN, O.V. CARD 1 / 2 PA - 1839 USSR / PHYSICS SUBJECT

On Measuring the Velocity of Surface Recombination in a thin Semi-LUTHOR conductor Sample with Qualitatively Different Boundary Surfaces. TITLE

Zurn.techn.fis, 26, fasc. 11, 2467-2472 (1956) PERIODICAL Issued: 12 / 1956

At first the continuity equations for the currents of holes and electrons in a semiconductor are written down in a general form. The present work investigates the solution of these equations for the concrete case that the following equations are satisfied: 1.) Stationary distribution of holes and electrons. 2.) Within the crystal domain investigated no holes or electrons are produced under the effect of external exciting factors. 3.) The crystal is assumed to be electrically neutral. 4.) The entire electric current passing through the crystal is assumed to be equal to zero. The following relations then hold good in the case of any geometric con-

 $\vec{I}_p = -qD \nabla \Delta p$, $\vec{I}_n = -qD \nabla \Delta n$ with $D = (n+p)/((n/D_p) + (p/D_n)$. Here \vec{I}_n and \vec{I}_p denote the current density of electrons and holes respectively, q - the absolute value of the electron charge, n and p - concentration of electrons and holes respectively, D and D - diffusion coefficients of electrons and holes respectively, τ - life of additional current carriers. The aforementioned continuity equations are then simplified as follows: $\Delta p/\tau = -q^{-1} \operatorname{div} I_p$, $\Delta n/\tau = q^{-1} \operatorname{div} I_n$. If the

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SOROKIN, O.V.

SUBJECT

USSR / PHYSICS

CARD 1 / 2

PA - 1840

AUTHOR TITLE

On Measuring the Life of the Diffusion Coefficient and of the Ve-

locity of the Surface Recombination of Current Carriers not in

Equilibrium in a Thin Semiconductor Sample Zurn. techn.fis, 26, fasc.11, 2473-2479 (1956)

PERIODICAL

Issued: 12 / 1956

A bundle of light, which produced electrons and holes in the semiconductor, moves above the here investigated plane, thin semiconductor sample with constant velocity. The author investigates the distribution of the current carriers which are not in equilibrium over the volume of the semiconductor sample for the concrete case that the following conditions are satisfied: 1.) The crystal is electrically neutral, 2.) No electric current passes through the crystal. The following continuity equations then hold good in the case of any geometric conditions of the samples: $(\partial/\partial t) \triangle p = D \operatorname{div} \nabla \triangle p - (\triangle p/\tau) + g$, $(\partial/\partial t) \triangle n = D \operatorname{div} \nabla \triangle n - (\triangle n/\tau) + g$. Here it holds that $D = (n+p)/((n/D_p) + (p/D_n))$, and D_n and D_p denote the diffusion p - concentration coefficient of the electrons and holes respectively, of electrons and holes respectively, Δ n and Δ p - concentration of excess electrons and holes (which are not in equilibrium, τ - life of current carriers which are not in equilibrium, g - production velocity of electrons and holes in the volume unit under the effect of external exciting factors. \triangle n and \triangle p are considered to be sufficiently small quantities. It is now shown that the same bound-

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SOROKINO.V.

AUTHOR:

SOROKIN,O.V.

TITLE:

Squaring of an Electric potential by means of the Semiconductor Device. (Kvadratirovaniye elektricheskogo napryazheniya pri prao-

shchi poluprovodnikovogo ustroystva, Russian)

PERIODICAL:

Radiotekhnika i Elektronika, 1957, Vol 2, Nr 5, pp 664-665 (U.S.S.R.)

109-5-20/22

ABSTRACT:

Reference is made to the paper by G.YE.PIKUS in Zhurnal Tekhn.Fiz. 1956, Vol 26, pp 22-50. The equation set up there for the modification of the specific electric resistance of a semiconductor sample in the magnetic field has a second term, which is proportional to EH, besides the usual term, which is proportional to H2. Here the formula for the second term is set up for the case in which the field H is directioned parallel to the axis oz while the electric field E is directioned parallel to the axis ox, and it is said that, according to experimental results obtained by the author, the ranges of application for this formula are in reality not so rigid as desoribed in the aforementioned paper by PIKUS. (With 2 Illustrations

and 1 Slavic Reference).

ASSOCIATION:

Institute for Semiconductors of the Academy of Science of the

U.S.S.R. (Institut poluprovodnikov Akademii nauk SSSR)

PRESENTED BY:

SUBMITTED:

22.11.1956

AVAILABLE:

Library of Congress

Card 1/1

SOROKIN, O.V.

109-10-9/19

AUTHOR: 'Sorokin, O.V.

TITIE:

Square Law Detection by Means of a Semi-conductor Device (Kvadratichnoye detektirovaniye pri pomoshchi

poluprovodnikovogo ustroystva)

Radiotekhnika i Elektronika, 1957, Vol.II, No.10, pp. 1293 - 1294 (USSR). PERIODICAL:

ABSTRACT: On the basis of the theory derived by G.E. Pikus (Ref.1), it is assumed that the change in the resistance of a semiconductor plate situated in/magnetic field H (see Fig.1) is expressed by Eq.(1). If a voltage U = U cos wt is applied to the plate in the direction of the axis x (see Fig.1) via an external resistance R, the voltage across the plate is in the form:

$$U_{r} = V_{o} + U_{\omega} \cos \omega t + U_{2\omega} \cos 2\omega t , \qquad (3)$$

 V_o is the DC voltage-component. It is shown that: where

$$v_0 = A v_0^2 \qquad , \tag{5}$$

from which it follows that the device can be used as a multi-The validity of Eq.(5) was checked experimentally for plier. Card1/2

SUBJECT USSR / PHYSICS CARD 1 / 2 PA - 1992

AUTHOR ZUZE, V.P., PIKUS, G.E., SOROKIN, O.V.

TITLE On the Problem of the Influence exercised by an Exterior Electro-

on the Problem of the Influence Surface Recombination in Germanium.

PERIODICAL Zurn. techn. fis, 27, fasc. 1, 23-29 (1957)

Issued: 2 / 1957

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Experimental method and results: The velocity of surface recombination was measured by the methods developed by O.V.SOROKIN, Zurn.techn.fis.26,11 (1956). On this occasion the effective diffusion lengths L_{α} were experimentally determined, and from the values found in this way the velocities of surface recombination were computed. Investigations were carried out with rectangular plates made of monocrystalline n- and p-germanium. The upper boundary surface of the sample served for the mounting of metal probes: phosphorus bronze for n-germanium and tungsten for p-germanium. On the upper boundary surface of the sample a rectilinear stripe of \sim 0,005 cm width, which was vertical to the longitudinal axis of the sample, was illuminated. A mica plate which was coated with silver on one side and had a thickness of from 0,0022 - 0,0030 cm was pressed or pasted on to the lower boundary surface. An electric voltage of up to 6 kV was applied to this silver coating. The block scheme of the measuring device is shown in form of a drawing. A diagram illustrates the typical curve which is obtained on the screen of the oscillograph by bringing aprobe into contact with the sample. When applying an exterior electric field to the sample the curve partly changed its shape,

Schoking, O.V.

AUTHOR TITLE ZHUZE, V.P., PIKUS, G.Ye., SOROKIN, O.V.

The Determination of the Surface Recombination Rate by Means of a Change of Semiconductors Resistance in the Lagretic Field.

(Metod izmeraniya skorosti poverkhnostnoy rekombinatsii po izmeneniyu soproti/leniya poluprovodnika v mag..itnou pole -Russain)

Zhurnal Tekh .Fiz., 1957, Vol 27, Nr 6, pp 1167-1173 (U.S.S.R.)

PERIODICAL

ABSTRACT

A new method for the measurement of the velocity of surface recombination is described. It is based on the dependence of the resistance of a semiconductor sample in a magnetic field on the recombination velocity on its surfaces. The results of experimental chekings of this method are given. They agree well with theoretical predictions; i.e. they fully prove the theoretical final conclusions mentioned in the work of one of the authors (G.Ye. Pikus, T, 1956, Vol 26, pages 22-50) with regard to the dependence of the semiconductor-resistance in the magnetic field on the velocities of the surface-recombinations, the voltage and the frequency of the electric field, as well as on the voltage of the magnetic field. The method presented can be used for the investigation of the influence of an exterior electrostatic field and of the outer medium on the velocity of surface recombination. At present such experiments are carried out and will be published later an various works. (1 table, 6 illustrations and 3 Slavic references).

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SOROKIN,

AUTHOR:

Sorokin, 0.V.

57-12-10/19

TITLE:

A Method of Measuring the Volumetric Lifetime and Diffusion Coefficient of Current Carriers by the Change of Resistance of a

(Metod izmereniya ob"yemnogo vremeni zhizni i koeffitsiyenta Semiconductor in the Magnetic Field

diffuzii nositeley toka po izmeneniyu soprotivleniya

poluprovodnika v magnitnom pole).

PERIODICAL:

Zhurnal Tekhnicheskoy Fiziki, 1957, Vol. 27, Nr 12,

pp. 2774-2776 (USSR)

ABSTRACT:

Semiconductors possessing positive and negative current carriers permit the observation of a special modification of resistance (reference 1 - 3) in a magnetic field apart from the ordinary increase of resistance connected with a decrease of the current carrier mobility and which is proportional to the square of the potential of the magnetic field. This effect is caused by a deviation of the carrier concentration from the equilibrium concentration in the case of current conduction by the semiconductor placed in a magnetic field. According to reference 1 the quantity $\theta_2 = f(d, D, T, J)$ on otherwise unchanged conditions is a

Card 1/3

A Method of Measuring the Volumetric Lifetime and Diffusion Coefficient of Current Carriers by the Change of Resistance of a
Semiconductor in the Magnetic Field

unique function of the thickness d of the sample, of the ambipolar diffusion coefficient D, of the volumetric lifetime 7 of the current carriers and of the frequency of the electric current in the sample. If the frequency-dependence of the effect obtained experimentally, that is $V_0 = V(V)$ or $E_{2V} = V(V)$, is compared with the theoretical dependence $V_2 = f(d, D, Z, V)$, D and can be determined. Adenotes a coefficient, which is independent of the external magnetic field strength and of the electric field strength in the sample. If $V_1 = V_1 = V_2 = V_1 = V_2 = V_1 = V_2 = V_2 = V_1 = V_2 = V_1 = V_2 = V_2 = V_1 = V_2 = V_1 = V_2 = V_1 = V_2 = V_1 = V_2 = V_2 = V_2 = V_1 = V_2 = V$

Card 2/3

SOROKIN, O.V.

103-2-7/9

-AUTHORS:

Pikus, G. Ye., Sorokin, O. V. (Leningrad)

TITLE:

A Non-Linear Semi-Conductor Resistance Sensitive to Magnetic Fields (Nelineynoye poluprovodnikovoye soprotivleniye,

chuvstvitel noye k magnitnomu polyu)

PERIODICAL:

Avtomatika i Telemekhanika, 1958, Vol. 19, Nr 2, pp. 187-188

(USSR)

ABSTRACT:

This is a letter to the editor. With reference to References 1 - 6 the formula (1) is put down and the characteristics of a linear germanium resistance with electron-conduction is investigated. At room temperature the equation (2) is then obtained ... $\Delta r = 0.083 \times 10^{-3} r$ UH, where Δr denotes the

complete variation of the electric resistance with the sample on different conditions (according to References 1 - 6). r denotes the resistance of the sample when there is no electric field present. Both are expressed in Ohms. U denotes the

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electric voltage at the sample in Volts. H denotes the strength of the magnetic field in Oersted. When the sample

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A Non-Linear Semi-Conductor Resistance Sensitive to Magnetic Fields

is located within the field of a constant magnet with H =1200 the total resistance $r=r_0(1+0.1\ U)$. An useful property of these non-linear resistances is the fact that the sign of the change of resistance, as it is to be seen from these formulae, depends on the direction of the electric- as well as of the magnetic field. The degree of non-linearity of the resistance can be increased if in place of a constant magnet an electromagnet is used which is fed from the same sources from which the resistances themselves are fed. In this case also the dependence of Δr on H is made use of. The magnetic field strength is changed and thus the magnitude of the change of resistance can be independently influenced. There are 6 references, 6 of which are Slavic.

SUBMITTED:

Hay 14, 1957

AVAILABLE:

Library of Congress

1. Electrons-Conduction-Mathematical analysis

Card 2/2

SOROKIN, O. V., Candidate Phys-Math Sci (diss) -- "The magnetic-concentration effect and its use for investigating the surface properties of a semiconductor". Leningrad, 1959. 15 pp (Leningrad Order of Lenin State U im A. A. Zhdanov), 200 copies (KL, No 24, 1959, 127)

67395 SOV/181-1-9-17/31

AUTHORS:

Zhuze, V. P., Pikus, G. Ye., Sorokin,

TITLE:

Application of the Magnetostriction Effect to the Investigation of the Surface of Semiconductors 7

PERIODICAL:

Fizika tverdogo tela, 1959, Vol 1, Nr 9, pp 1420 - 1430 (USSR)

ABSTRACT:

The authors used the method of surface recombination rate measurement by means of the resistance change of a semiconductor in the magnetic field to investigate the energy surface structure of germanium. This investigation is reported here in all details. The method applied to measure the surface recombination rate is new and was introduced by the authors themselves. A description thereof is given in references 4 and 5. The aim of the investigation under review was that of demonstrating the application of this method, with two samples of n- and p-germanium being used for the purpose. Figure 1 shows the block diagram of the used setup. The method is based on the application of a formula describing the relation between the resistance change $\Delta \varrho_{H}$ of a thin plane

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sample in the magnetic field H and the recombination rates s

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Application of the Magnetostriction Effect to the Investigation of the Surface of Semiconductors

SOV/181-1-9-17/31

and s₂ on their opposite faces: $\Delta Q_H/Q_0 = 2A G_y H \frac{s_1 - s_2}{s_1 + s_2 + \alpha/\tau}$, where d is the sample thickness, G_y the voltage of the main frequency), which is incident upon the investigated part of the sample, G_0 is the resistivity without magnetic field. A is given by $A = \frac{s_n}{4} \frac{e\mu_n}{ckT} \frac{(1+b)(1+\rho b)p_n}{(n+pb)} \frac{d}{1}$, where n and p denote the equilibrium concentrations of electrons and holes, μ_n and μ_p their drift mobility, $a_n\mu_n$ and $a_p\mu_n$ their Hall mobility, and 1 the length of the investigated part of the sample. It is now described how it is possible, by means of the instrument, to obtain direct oscillograms reproducing the dependence of $a_1 - a_2 - a_1 + a_2 - a_2 - a_1 + a_2 - a_2 - a_1 + a_2 - a_2 -$

the quantity $\frac{81^{-8}2}{81^{+8}2^{+\alpha/\tau}}$ on the applied field. Figures 2-5 show

such oscillograms for the two samples investigated, whose characteristics are given. The next section discusses the

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Application of the Magnetostriction Effect to the Investigation of the Surface of Semiconductors

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interpretation of measuring results in detail; the results are given in the form of diagrams, and the numerical values are given in two tables. The method described is very expedient for a quick and fairly accurate determination of the field-bound change of s. A. V. Rzhanov, I. A. Arkhipova, and V. N. Bidulya (Ref 12) applied this method to investigate the modulation of s through an outer electric field. Their results, however, did not fit those by the authors in two points. This is discussed in the final part of the paper. There are 10 figures, 2 tables, and 15 references, 8 of which are toylet.

ASSOCIATION

Institut poluprovodníkov AN SSSR Leningrad (Institute of Bemiconductors of the AB USBN, Leningrad)

SUBMITTED:

February 16, 1959

Card 3/3.

AUTHOR: Sorokin, 0.V. SOV/120-59-2-20/50

TITLE: An Instrument for Examining Transients on the Surfaces

of Semiconductors (Ustanovka dlya issledovaniya

perekhodnykh protsessov na poverkhnosti poluprovodnika)

PERIODICAL: Pribory i tekhnika eksperimenta, 1959, Nr 2,

pp 68-75 (USSR)

ABSTRACT: Surface conductivity and surface recombination are

examined by using the changes in carrier concentration produced by an external magnetic field. The first part of the paper (to Eq (7)) deals with the theory. An

external electric field is used to perturb the

equilibrium state of the semiconductor; this field is such as to induce a surface charge density of 1.25x1011 electron units per cm2. The field is varied rapidly

electron units per cm². The field is varied rapidly (at a frequency of 3.5 kc/s) to examine the fast changes, and by simple switching to examine the slow changes.

The current through the specimen is fixed by inserting a large series resistance; the voltage drop across the specimen is measured. A differential amplifier of gain

Card 1/3 about 2000 and of pass band from 10 c/s to 10 kc/s is used to eliminate the parasitic signal resulting from

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SOV/120-59-2-20/50

An Instrument for Examining Transients on the Surfaces of Semiconductors

capacity pick-up (the gain for signals in the same phase at both inputs is less than 1). A special cathode follower with a double π -type LC filter precedes the Special precautions are taken to filter the alternating coltage very thoroughly in order to eliminate interference from high harmonics, which are very readily transferred from the high-voltage source producing the external electric field to the input of the amplifier. The magnet is used to alter the carrier concentration, which alters the mean lifetime and hence the concentration, A few results are but does not affect the mobility. given for Ge to illustrate the operations of the differential amplifier and other units. (The circuits are those given by Madelung and Banbury, Refs 14 and 16, with certain minor improvements, the main one of which

Card 2/3 is an improved device for balancing out the parasitic

SOV/120-59-2-20/50 An Instrument for Examining Transients on the Surfaces of Semiconductors

signal to the differential amplifier). There are 14 figures and 18 references, of which 11 are Soviet, 5 are German and 2 are English.

ASSOCIATION: Institut poluprovodníkov AN SSSR (Institute of Semiconductors, Ac.Sc. USSR)

SUBMITTED: March 3, 1958

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SORCKIN, O.V.

S/181/60/002/007/023/042 B006/B060

AUTHORS:

Sorokin, O. V., Tuseyev, B. T.

TITLE:

Comparative Study of the Magnetic Concentration Method and the Photoelectric Method of Measuring the Surface

Recombination Rate

PERIODICAL:

Fizika tverdogo tela, 1960, Vol. 2, No. 7, pp. 1533-1535

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TEXT: In continuation of previous papers the authors report here on their measurements of the surface recombination rate by means of two methods that had been already discussed in Refs. 1, 6. As was measured from the second harmonic with a setup described here, whose block diagram is shown in Fig. 1. The function of the various blocks is discussed and some problems concerning calibration are briefly dealt with. Prior to the measurements proper concerning the modulation of the surface recombination rate by the method of the "traveling light beam", the minority carrier lifetime and the diffusion coefficient were measured among other things. After experiments on modulation, the surface under examination was ground, and the surface recombination rate was again measured by the method of the

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Comparative Study of the Magnetic Concentration S/181/60/002/007/023/042 Method and the Photoelectric Method of Measuring B006/B060 B066

"traveling light beam" (Refs. 3, 8). The results were compared. Fig. 2 shows a comparison of results concerning the variation with time of the surface recombination rate, obtained by the method of the second harmonic (full line) and obtained by the method of the "traveling light beam" (dots). Highly homogeneous single crystals of n-type germanium were used for the experiments. The initial s-value was s=600 cm/sec. It is established from the investigations that both methods lead to correct results. There are 2 figures and 13 references: 11 Soviet and 1 German.

ASSOCIATION:

Institut poluprovodnikov AN SSSR Leningrad

(Institute of Semiconductors of the AS USSR, Leningrad)

SUBMITTED:

December 4, 1959

Card 2/2

25689

3/181/61/003/007/011/023 B102/B214

Petrusevich, V. A., Sorokin, O. V., and Kruglov, V., I.

TITLE:

AUTHORS:

Applicability of the parameter of the "effective surface

recombination rate" for Ge and Si

PERIODICAL: Fizika tverdogo tela, v. 3, no. 7, 1961, 2023-2030

TEXT: The object of the authors was to demonstrate experimentally that cases in which the parameter of the "effective surface recombination rate" cannot be used for the characterization of the Si surface are realizable in practice, and that this parameter can be used generally for the characterization of Ge surfaces treated by the usual etching agents. fact that the application of the effective surface recombination rate S is not always justified has been referred to by Shockley and Read (Phys. Rev. 87, 835, 1952). Also the conditions of applicability of this . parameter were theoretically studied earlier. The authors of the present paper investigated n-type and p-type germanium with a conductivity close to intrinsic conductivity, and also n-type and p-type silicon with resistivities of 10 to 130 ohm cm. After establishing the ohmic contacts the surfaces of the individual samples were treated differently, i. e., Card 1/6

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Applicability of the parameter ...

etched by different agents and under different conditions. The method of measuring the field effect has been described elsewhere by Sorokin (PTE, No. 2, 60, 1959). The change of conductivity related to the change of Y was determined from the field effect, and thus Seff was found out.

Indeed, $S_{eff} = \frac{1}{10} - \frac{$

to the blocking and inversion barriers, and the negative values to the anti-blocking barriers. Of particular interest are the results for Si, as only hypothetical data exist on the effects of the above-mentioned etching agents. For example, a strong blocking or even an inversion layer appears on p-type Si after it has been etched according to method 4, while either a weakly blocking or an anti-blocking barrier appears in n-type Si. All Card 2/6

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Applicability of the parameter ...

experiments were carried out in room atmosphere. The Table also contains data on the surface recombination rate calculated from the curves of the spectral distribution of photoconductivity. The following conclusions can be drawn from the results: 1) For sufficiently high surface potential barriers and the usual values of the diffusion length, a case is realizable in practice in which the notion of Seff loses all sense. The higher the resistance of the sample, the lever is the value of Y for which this will be the case, because increases with C. It is, therefore, to be expected that for semiconductors having a forbidden band width larger than that of germanium, the parameter Seff will not be applicable for relatively small Yo. 2) All conclusions which are based on the application of Seff or test should be revised, and it should be investigated whether the criteria for the applicability of Seff are fulfilled. This holds, above all, for the band structure of surface semiconductors with which Seff or Teff used as a function of Yo. 3) It is necessary to improve the theory of Card 3/6

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S/181/61/003/007/011/023 B102/B214

Applicability of the parameter ...

effects in which surface properties are involved, and to determine the role of the geometry of the potential barrier. 4) The criteria for the applicability of Seff should also be improved. Above all, it should be kept in mind that T in the surface charge layer is in general not equal to T in the volume of the semiconductor. The authors thank G. Ye. Pikus, and G. L. Bir for discussions. There are 4 figures, 1 table and 14 references: 9 Soviet-bloc and 5 non-Soviet-bloc.

ASSOCIATION: Institut poluprovodnikov AN SSSR Leningrad (Institute of Semiconductors, AS USSR, Leningrad)

SUBMITTED: January 14, 1961 (initially) and February 10, 1961 (after revision)

Card 4/6

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..., EWT(1)/EWP(q)/EWT(m)/BDS AFFTC/ASD/ESD-3/IJP(C) GG/JD/JG

ACCESSION NR: AT3002450

AUTHOR: Petrusevich, V. A.; Sorokin, O. V.

Effective rate of surface recombination and criteria of its applica-

bility [Conference on Surface Properties of Semiconductors, THE TITLE: Institute of Electrochemistry, AN SSSR, Moscow, 5-6 June, 1961]

SOURCE: Poverkhnostnyve svoystva poluprovodnikov. Moscow, Izd-vo AN SSSR,

1962, 164-174

TOPIC TAGS: recombination, surface recombination, semiconductor-surface

recombination

ABSTRACT: Experimental verification of theoretical conclusions arrived at by G. L. Bir (Physics of solid-state body, 1, 67, 1959) is reported. Criteriz of applicability of the effective rate of surface recombination (ERSR) have been nutablished; the effect of the geometry of the near-surface space charge upon the spectral distribution of photoconductivity (SDPC) and photomagnetic effect (PME) has been clarified. Near-intrinsic-conductivity Geland 10-130-ohms-cm Si were used in the experiments. Usual etching methods caused high surface

Card 1/2

L 18990-63

ACCESSION NR: AT3002450

potential barriers in Ge and Si. The diffusion length and coefficient of ambipolar diffusion measured by SDPC and PME methods gave very close results, while ERSR values measured by the same methods differed widely. In some cases, theoretical and experimental SDPC curves did not agree. Hence, ERSR is inapplicable in many important practical cases, such as the treated surface of Si. On the basis of the above facts, more accurate formulas for computing parameters of SDPC and PME have been developed by the authors. "In conclusion, the authors are deeply grateful to G. Ye. Pikus and G. L. Bir for their interest in the work and useful advice." Orig. art. has: 4 figures and 19 formulas.

ASSOCIATION: Institut poluprovodnikov AN SSSR (Institute of Semiconductors, AN SSSR)

SUBMITTED: 00

DATE ACQ: 15May63

ENCL: 00

SUB CODE: PH

NO REF SOV: 008

OTHER: 005

Card 2/2

S/109/63/008/002/010/028 D413/D308

AUTHORS:

Iorish, A.Ye., Krasin'kova, M.V., Moyzhes, B.Ya.,

and Sorokin, O.V.

TITLE:

The thermal emf, electric conductance and resistance variation in a magnetic field of barium-strontium

oxide

PERIODICAL:

Radiotekhnika i elektronika, v. 8, no. 2, 1963,

269-278

TEXT: Although a number of papers have dealt with measurements of thermal emf, $\Delta \rho/\rho$ in a magnetic field, and electrical conductance of cathode oxide coatings, these data have been considered in isolation. Here they are all examined together in the light of the accepted theory that conduction in oxide coatings occurs through the pores, which are filled with electron gas by thermionic emission from their walls. First a theoretical treatment is given for the values of thermal emf, conductance and $\Delta \rho/\rho$ for the electron gas in the pores, and then experimental results for barium-strontium exide

Card 1/2

The thermal		S/109/63/008/002/010/028 .D413/D308			
weak magneti bottom of th	c fields is c ne conduction eviment conduct	ed. The linear explained: the valuation is evaluated are calculated. There are 8	ted: the dim lated with a	ensions of	the
SUBMITTED:	April 26	i, 1962			
Card 2/2					

	AP4017600		5/0109/64/009/002/0300/030			
ion nr:						

OR: Dubova, T. A.; Iorish, A. Ye.; Krasin'kova, M. V.; Dubova, T. A.; Iorish, A. Ye.; Krasin'kova, M. V.; Chudnovskiy, F. A.; B. Ya.; Petrov, I. N.; Sorokin, O. V.; Chudnovskiy, F. A.

Electrical conductivity and thermo-emf of a barium-strontium oxide in

SCORGE: Radiotekhnika i elektronika, v. 9, no. 2, 1964, 300-307

OPIC TAGS: electrical conductivity, thermo emf, oxide coated cathode, the strong stron

ABSTRACT: Measurements were taken of factory specimens of Ba-Sr oxide, 100-200-microns thick, placed between two cylindrical nickel bases (see Enclosure 1) and subjected to a transverse magnetic field. One of the tubes was equipped with a ring anode and served to measure the thermo-emission from the

Card 1/12

ACCESSION NR: AP4017600

resistivity and thermo-emf of the Ba-Sr oxide was investigated. Estimated from experimental results, the free-path length of an electron in the cathode pores is 4-30 microns and the electron mobility is from 3.5 x 10⁴ to 2 x 10⁵ cm²/v sec for the various specimens. The thermodynamic work function, electron concentration, and conductivity are also estimated. It is inferred that the cores in the oxide cathode must be open and intercommunicating and, therefore, that under total thermionic-current conditions, the electrons must be emplain the abnormally high Schottky effect in oxide cathodes. Orig. art. has: 7 figures, 13 formulas, and 1 table.

ASSOCIATION: none

SUBMITTED: 30Dec62

DATE ACQ: 18Mar64

ENCL: 01

SUB CODE: GE

NO REF SOV: 001

OTHER: 003

Card 2/37

ACCESSION NR: AP4043679

S/0109/64/009/008/1447/1457

AUTHOR: Iorish, A. Ye.; Moyzhes, B. Ya.; Sorokin, O. V.;

Chudnovskiy, F. A.

TITLE: Temperature distribution in a cathode oxide coating

SOURCE: Radiotekhnika i elektronika, v. 9, no. 8, 1964, 1447-1457

TOPIC TAGS: oxide cathode, electron tube, electron tube cathode,

(BaSrCa)CO3 cathode, (BaSr)CO3 cathode

ABSTRACT: The theoretical and experimental investigation of the temperature distribution in an oxide-coated cathode is reported. The theoretical part differs from the well-known work of H. C. Hamaker (Philips Res. Repts., 1947, 2, 55-67, 103-111, 112-125) in that the temperature drop in the oxide is not assumed small, and an allowance is made for the Joule heat in the oxide, for the refractive index of the oxide, and for the radiation reflected by the anode. The experimental part includes measuring the thermal conductivity $(10^{-5}-3\times10^{-6} \text{ w/cm-degree})$ of oxide-coating grains at temperatures ranging from room temperature

Card 1/2

ACCESSION NR: AP4043679

down to liquid-nitrogen temperature. It is estimated that the temperature of the oxide may be higher than that of the cathode base by hundreds of degrees when heavy emission currents are involved; a still higher difference is possible under pulsed operating conditions of the tube. The anode reflection has an essential effect on the temperature distribution. Hot spots on the cathode due to low thermal conductivity at heavy emission or due to an insufficient rate of heat removal from an underheated cathode may result in sparking; a formula giving a criterion of the cathode thermal instability is offered. The heat radiation capacity of a Ni-base oxide cathode was measured; the radiation dissipation factor, which corresponds to a photon free-path length of 30-50 microns at 800-900C, is estimated. Orig. art. has: 5 figures, 31 formulas, and 2 tables.

ASSOCIATION: none

ENCL: 00

SUBMITTED: 15Jun63

OTHER: 011

SUB CODE: EC

NO REF SOV: 005

Card 2/2

CIA-RDP86-00513R001652510011-9" APPROVED FOR RELEASE: 08/23/2000

s/0020/64/157/006/1325/1328

AP4044875 ACCESSION NR:

AUTHOR: Sorokin, O. V.; Samarin, Yu. P.; Oding, I. A. (Deceased, Corresponding member AN SSSR)
TITLE: Design for creep of beams under flexure

SOURCE: AN SSSR. Doklady* v. 157, no. 6, 1964, 1325-1328

TOPIC TAGS: creep, beam flexure, beam creep, creep analysis, bending creep, flexural creep

ABSTRACT: The creep of a beam under pure flexure is analyzed by linearizing the set of equations describing a four-element elastoviscous model used in investigation of problems associated with deformation of materials at high temperatures. It is assumed that the elastic and viscous characteristics of the model materials are stress- and time-dependent (obtained by creep testing under constant stress) and can be represented by piecewise-constant functions. The initial set of equations is thus converted into a linear one with discontinuous coefficients. The procedure of the creep

ACCESSION NR: AP4044875

analysis is outlined and illustrated by an example. A way of simplifying the method by replacing the variable characteristics of the model by their averaged quantities is indicated, and the equation of the curvature of the neutral axis of the beam is given. The single terms in this equation show the amount of elastic, elastoplastic, and plastic deformation. The authors regret that because of lack of experimental data no conclusion can be made on the feasibility and applicability limits of this method. Orig. art. has: 4 figures and 12 formulas.

ASSOCIATION: none

SUBMITTED: 19Nov63

ATD PRESS: 3090

ENCL: 00

SUB CODE: AS

NO REF SOV: 002

OTHER: 000

Card 2/2

SOROKIH, C.V.; IF MACHEV, Ya.T.

Metics for fast loading of specimens in tensile tests.

Zev.lat. 31 no.3:381-382 '65. (NIRA 18:12)

1. Kuybyshevskiy politakhnicheskiy institut.

B

L 14824-65 EWT(m)/EWF(w)/EWA(d)/EWP(t)/EWP(b) ASD(f)-2/SSD/AFWL/AFTC(p)
JD
ACCESSION NR: AP4048030 S/0020/64/158/006/1285/1286

AUTHORS: Sorokin, O. V.; Oding, I. A. (deceased; Corresponding

member AN SSSR)

TITLE: Concerning creep under pulsating stress

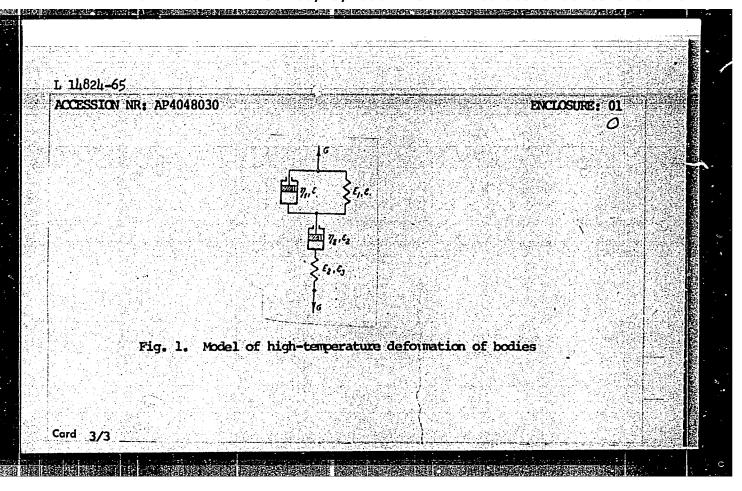
SOURCE: AN SSSR. Doklady*, v. 158, no. 6, 1964, 1285-1286

TOPIC TAGS: creep characteristic, creep mechanism, stress analysis, strain measurement, rate of deformation

ABSTRACT: It is shown that the strain-time curve under pulsating stress can be derived from the creep curve obtained under time-constant load, by simulating the high temperature deformation process by a system consisting of two elastic and two viscous elements, as shown in Fig. 1 of the enclosure. A graphic construction for plotting the strain-time is demonstrated. This analysis explains how creep is affected by intermissions during the tests and how seem-

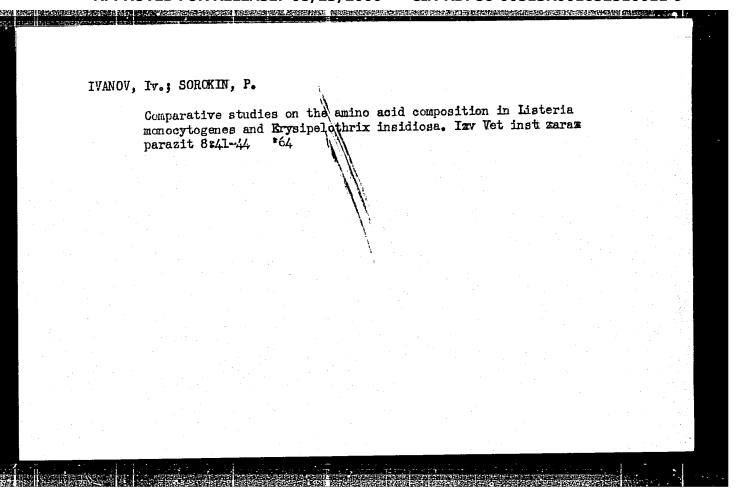
Card 1/3

L 14824-65			100
ACCESSION NR: AP404803	30		
tarana and under ctross	behavior of material under of relaxation still lead to realculations. Orig. art. has	Sputce cuer adree	
ASSOCIATION: Kuyby*she Kuyby*she (Kuyby*she)	evskiy politekhnicheskiy ins v Polytechnic Institute)	titut im. V. V.	
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	NR REF. SOV: 000		



SAVOV, N.; SOROKIN, P.; KALUCHEVA, Iv.

Studies of various mycobacteria isolated from animals having reacted to tuberculin. Izv Vet inst zaraz parazit 8:17-24 064



Biosynthesis of citric acid by means of Aspergillus niger. Ecklady
BAN 17 no.6:581-584 '64.

1. Submitted by Corresponding Member D. Mateev.

SCRCKIN, F. A.

Sorokin, P. A. - "Change in the cardiovascular system during acute hepatitis,"
Sbornik trudov (Voyen.-med. akad. im. Kirova), Vol. XLIII, 1949, p. 140-43

SO: U-43:5, 14 August 53, (Letopis 'Zhurral 'nykh Statey, No. 15, 1949.)

T : Human and Animal Physiology, Circulation Country Catogory= Abo. Jour. : Ref Zhur Biol, No. 2, 1959, No. 8060 :Sorokin.P.A.; Mitropol'skiy, A.N.; Gadzhiyev S.A. M. Burn :Blestkina T.G. :Changes in Certain Indices of the Functional Inestado. State of the Cardiovascular System in Patients Title with Mitral Stenosis After Commisurotomy. Orig. Pub. : Terapevt. arkhiv, 1957, 29, No. c, 3--9. The study included 50 patients ranging in age from 17 to 43. Prior to surgery it was Abstract established that in 41 of the patients mitral insufficiency was present as well as stenosis, while the other 9 had pure mitral stenosis. In 46 patients the stenosis was of grades III and IV, and in the other 4 it was of grade II. The status of the circulation was evaluated by means of the arterial and vencus pressure (the Waldman method) and cardiac systolic volume, determined by the N.N.Savitskiy mechanocardiograph and acetylene method or calculated from Starr's

APPROVED FOR RELEASE: 08/23/2000 CIA-RDP86-00513R001652510011-9" Human and Animal Physiology, Circulation

Clinic Fac. Therapy 1/2 Surgical Clinic for advanced Physician, Will-Med acad in Kir

Abs. Jour. : Ref Znur Biol, No. 2, 1959, No. 8060

Title

* Office yo

Orig Pub.

Abstruct :formula. One to two months after commisurotomy grade I mitral stenosis was detected in 5 patients, grade II in 31 patients, grade III in 11 and grade IV in 3. Six months to 22 years following the operation signs of grade I mitral stenosis were found in 3 out of the 25 patients followed, grade II in 17, grade III in 3 and grade IV in 2. The absence of improvement in cardiovascular function in 5 patients the author explains by postoperative complications and inadequate dilatation of the mitral orifice .--T.S. Vinogradova 2/2

Card:

Pe-5 AFFTC/AFMDC/AMD/APGC DD UR/3147	/64/003/000/0091/0105	
AUTHOR: Gramenitskiy, P. M.; Sorokin, P. A.	26 BH	
FITLE: Mechanism of changes in respiration and coxygen under high pressure	irculation in dogs exposed te	
SOURCE: AN SSSR. Institut evolyutsionnoy fiziol usloviyakh izmenennoy gazovoy sredy, v. 3, 1964,	logii. Funktsii organizma ▼ 91-105	
TOPIC TAGS: oxygen poisoning, high pressure respondent, oxygen	piration, circulation pressure	
ABSTRACT: The authors studied 17 dogs weighing l	12—17 kg under urethane anesthe-	
sia, administered in a 2/3 dose before and a 1/3 table. The average dose of administered uretha	ne was 1. 2 g/kg. In cases	
where respiration was accelerated, morphine wa	as administered. Heparin	
was also given to prevent coagulation in the bloo device. After anesthesia, tracheotomy was perf	formed and a canule was.	
introduced into the femoral artery to measure a	rterial pressure. The	
prepared animals were placed in a pressure cha graph for recording respiration; lung ventilation	moer containing a tymo	
Card 1/4		

L 42191-65

ACCESSION NR: AT5010604

EKG's were also recorded at various intervals throughout the experiments. The pressure in the chamber was maintained at 6 atm (except for the 3 control tests), and the dogs breathed nearly pure oxygen (nitrogen content, 1—2%). Exposure conditions varied according to the purpose of the tests.

A total of 26 tests were conducted. In 7 tests, animals with intact nervous systems were exposed to high oxygen pressures. In 11 tests, animals underwent vagotomy, resection of the subclavian loop, or complete cardiac denervation prior to the action of oxygen or at various periods during oxygen poisoning. In 8 tests, the splanchnic nerves were resected and the adrenal glands were ligatured. In all tests, the animals were observed for initial symptoms of oxygen poisoning.

The experiments revealed that the course of oxygen poisoning in anesthetized dogs could be divided into 4 periods. The first period was characterized by decreases in lung ventilation and cardiac activity and was adaptive in nature. The vagus nerve played the basic role in these protective reactions. The second, preconvulsive period was characterized by hyperventilation, tachycardia, and increased arterial pressure which re-

Card 2/4

L 42191-65 ACCESSION NR: AT5010604 flected the participation of the adrenosympathetic system. These reactions were deleterious, since they accelerated the onset of oxygen poisoning. In the third period, convulsions took place. This period was characterized by a gradual decrease in cardiac rhythm which became tachycardia as soon as convulsions occurred. At the end of this period there was a parasympathetic effect with a background of respiratory inhibition which led to bradycardia, nodal rhythm, or cardiac block. These disruptions of cardiac rhythm were reversible and could be eliminated by vagotomy. The fourth period was characterized by a sharp increase in blood pressure and accelerated cardiac activity (sinus tachycardia). When respiration had ceased, arterial pressure. fell but cardiac activity persisted. At the end of this period bradycardia and cardiac block occurred which could not be eliminated by vagotomy. It was found that preliminary resection of vagus nerves eliminated the decrease in cardiac activity during the first three periods of oxygen poisoning and therefore hastened the onset of convulsions and shortened the survival period of the animals. Preliminary ligature of the adrenals increased the survival time of dogs exposed to 6 atm oxygen and inhibited the development of convulsions. A similar but more pronounced effect was produced when splanchnic nerves were also eliminated. This effect can be explained Card 3/4

L 42191-65

ACCESSION NR: AT5010604

as a function of the removal of the adrenosympathetic system and the consequent increased blood deposition and, in connection with this factor, decreased blood supply to tissues as well as lowered oxidation processes. Following adrenal isolation and disruption of splanchnic and cardiac sympathetic nerves, those protective parasympathetic reactions noted in the cardiac activity of intact animals did not occur, in spite of the preservation of vagus nerves.

The authors conclude by commenting on the role of the adrenosympathetic system in reactions to high oxygen pressures. On one hand the system must play a significant role in toxic manifestations of high-pressure oxygen by inhibiting parasympathetic cardiovascular protective reactions. On the other hand, the system must participate in the development of these very protective reactions. Orig. art. has 6 figures and 1 table.

ASSOCIATION: none

SUBMITTED: 00

NO REF SOV: Oll

Card 4/4 /108

ENCL: 00

OTHER: 009

SUB CODE: LS, PH

ATD PRESS: 3240-F

ENG(j)/ENG(r)/ENT(1)/FS(v)-3/ENG(v)/ENG(a)-2/ENG(a) Pa-5 DD UR/3147/64/003/000/0106/0115 L 42001-65 ACCESSION NR: AT5010605 AUTHOR: Groshikov, M. A.; Sorokin, P. A. TITLE: Pathomorphological changes in the lungs of animals exposed to high oxygen prèssure SOURCE: AN SSSR. Institut evolyutsionnoy fiziologil. Funktsii organizma v usloviyakh izmenennoy gazovoy sredy, v. 3, 1964, 106-115 oxygen pressure, lung, oxygen effect, hemorrhage ABSTRACT: The changes caused by high oxygen pressure in dogs and guinea pigs are essentially the same. Expansion and hyperemia of the veins and capillaries, sometimes with hemorrhages in the surrounding tissues and in the lumens of the alveoli are observed in the lungs as well as perivascular edema, thickening of the interalveolar walls due to edema and dilatation of the capillaries, and varying degrees of atelectasis. Lung injury was combined with more or less pronounced congestion in the other viscera. Adrenalectomy in the dogs, especially when combined with division of the splanchnic nerves, reduced the pathological effects of high oxygen pressure on the lungs. This confirms the importance of humoral factors in pulmonary lesions resulting from acute oxygen poisoning. Division of the splanchnic

L 42001-65 ACCESSION NR: AT5010605		0	
by reducing the amount of cir	e viscera. Congestion and pulculating blood. This explains ctomy alleviates the adverse plas: 6 figures.	s why the combination of	
ASSOCIATION: none			
SUBMITTED: 00	ENCL: 00	SUB CODE: LS	
NO REF SOV: 007	OTHER: 012		
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ÉWG(1)/EWG(r)/EWT(1)/FS(v)-3/EWG(v)/EWG(a)-2/EWG(c) Pb-:/ AFFTC/AFMDC/AMD/APGC DD UR/3147/64/003/000/0116/0125 ACCESSION NR: AT5010606 Sorokin, P. A. AUTHOR: TITLE: Changes in cardiac electrical activity in animals exposed to high oxygen pressures SOURCE: AN SSSR. Institut evolyutsionnoy fiziologii, Funktsii organizma v usloviyakh izmenennoy gazovoy sredy, v. 3, 1964, 116-125 TOPIC TAGS: high pressure respiration, oxygen, pressure chamber, oxygen poisoning, cardiovascular system, bicelectricity, EKG ABSTRACT: The authors studied the effects of oxygen poisoning on the heart bioelectricity of guinea pigs and dogs. The first series of experiments was conducted on intact guinea pigs placed on their backs and held rigidly in place by their hind quarters. Needle electrodes were fixed subcutaneously for the EKG pickup. The animals were situated in a 65-liter chamber in which the electrodes were connected to EKG leads. The first group of tests took place under pressures of 1, 0, 2, 0, and 3, 0 atm for 150-180 min (27 experiments). EKG's were registered before, during, and after pres-Card 1/4

L 42190-65

ACCESSION NR: AT5010606

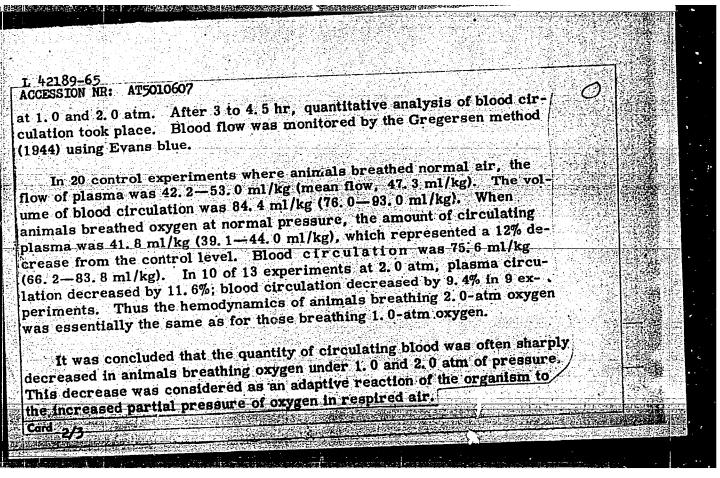
sure tests. In addition, heart bioelectricity was studied during convulsive forms of severe oxygen poisoning under pressures of 5.5 atm (16 experiments). In 8 experiments with guinea pigs at 5.5 atm, a 1-mg/kg solution of atropine was injected subcutaneously. In all tests, oxygen content ranged from 92 to 96% and carbon dioxide content from 0.05 to 0.2%.

The second series of experiments was conducted on dogs anesthetized with urethane. Of 15 experiments, 6 were on intact animals, 7 were on dogs vagotomized prior to the action of Oxygen, and 2 were on dogs which underwent cardiac denervation during severe, convulsive oxygen poisoning. All tests took place in a large pressure chamber in which animals were exposed to 6 atm. Nitrogen content did not exceed 2%. EKG's were recorded before, during, and after the tests.

The results of the experiment revealed that in the initial period of acute oxygen poisoning there was a sharp decrease in sinusoidal rhythm, often extrasystole, and also sinoauricular block and disruption of atrioventricular conductivity in intact guinea pigs. Cardiac block and, less often, nodal or idioventricular rhythm was observed during the convulsive Cgrd 2/4

L 42190-65 ACCESSION NR: AT5010606 period of oxygen poisoning. During the terminal period, sinusoidal tachycardia was observed in dogs which changed to bradycardia and transverse block when breathing had stopped. Preliminary atropine injections or resection of vagus nerves eliminated decreased cardiac rhythm, sinoauricular block, and disruption of atrioventricular conductivity, both in the initial and convulsive periods of acute oxygen poisoning, but did not prevent bradycardia or cardiac block in the terminal period. Sinusoidal tachycardia at the beginning of the terminal period followed heart block or heterotropic rhythm and was not eliminated by resecting sympathetic nerves leading to the heart. Displacement of the R(S)-T segment with negative "gigantic" T-waves during the simultaneous decrease in voltage of R spikes was considered as a manifestation of myocardial hypoxia which evidently developed as a result of tissue respiration inhibition during acute oxygen poisoning. The disruption of cardiac rhythm and other bioelectrical shifts which occurred during the convulsive period of acute oxygen poisoning were temporary in nature and quickly disappeared when high oxygen pressures were terminated Orig. art. has 5 figures.

L 42189-65 EWG(a)-2/EWG(c)/EWG(j)/EWG(r)/EWG(v)/EWT(1)/FS(v)-3 Pe-5 AFFTC/AFMDC/AMD/APIC DD UR/3147/64/003/000/0126/0131 ACCESSION NR: AT5010607 AUTHOR: Sorokin. P. A. TITLE: Change in the amount of circulating blood in dogs breathing oxygen under pressures of 1.0 and 2.0 atm SOURCE: AN SSSR. Institut evolvutsionnoy fiziologii. Funktsii organizma v usloviyakh izmenennoy gazovoy sredy, v. 3, 1964, 126-131 TOPIC TAGS: respiration, exygen, dog, pressure chamber, high pressure respiration, circulation ABSTRACT: The authors studied quantitative changes in blood circulation of dogs breathing pure oxygen at pressures of 1.0 and 2.0 atm. All experiments were performed in a pressure chamber. The dogs breathed both normal air and oxygen through masks while lying on their left sides. The amount of time between experiments for each dog ranged from 1 to 2 weeks so that conditioned reflexes to the respiratory mask would not develop. On the day of a typical test, dogs were weighed, placed in the pressure chamber with masks on, and given first normal air to breath and then oxygen Card 1/3



1, 42189-65			
ACCESSION NR: AT5010607			
Orig. art. has 3 figures as	nd 2 formulas.	0	
ASSOCIATION: none			
SUBMITTED: OO	EXCL: 00	SUB CODE: LS	. Pil
RO REP SOV: 003	•THER: 009	ATD PRESS: 32	10-F
M RESOLUTION			
74			
pse			
Card 3/3			

SOROKIN, P.G.	(2) LLCC 1954. On the extinction of arce in apparatus for the	
Electrical Engineering Abstracts May 1954 Switchgear	perfiching of high-power cally, direct current networks, G. A. Kurkerov and P. G. Schoen. Elektrichestro, 1953, No. 10, 20-4, in Restaurance of the perfect of experimental work on conventional compressed-air circuit breakers, assisted by an oscillatory circuit shinting the arc. The main decays simulated by 50 c/s currents of up to 125 A at 50 kV. The capacitor of the oscillatory circuit was initially charged to about 10 kV, freely oscillating at 300-1000 c/a, with a current amplitude of about double the main current. Oscillograms are given of the extinguishing action without and with the oscillatory circuit, and it is concluded that the method is applicable to 400 to 800 kV d.c. power switching.	
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sov/105-59-3-5/27

AUTHORS:

Kukekov, G. A., Candidate of Technical Sciences, Docent,

Sorokin, P. C., Engineer, Shipulina, N. A., Candidate of Technical

Sciences (Leningrad)

TITLE:

Switch-off Contactors for High-tension Direct Current Transmission Lines (Otklyuchayushcheye ustroystvo dlya liniy postcyannogo toka

vysokogo napryazheniya)

PERIODICAL:

Elektrichestvo, 1959, Nr 3, pp 24-27 (USSR)

ABSTRACT:

The use and the further development of d.c. long-distance transmission lines in many respects depends upon the creation of new electrical equipment and installations. Such devices include contactors designed to disconnect powerful and highly inductive hightension d. c. circuits. The principal difficulty encountered in this problem consists of the fact that it is much more difficult to suppress the flashover are in d. c. circuits than in a. c. circuits. In the course of the investigations carried out in the Leningradskiy politekhnicheskiy institut im. Kalinina (Leningrad Polytechnical Institute imeni Kalinin) and at the Institut postoyannogo toka (Institute of Direct Current) (Refs 1,2) it was found that

if the d. c. arc is shunted by an oscillation circuit with corresponding parameters and initial conditions - the current in the

Card 1/3

,我们是是一个人,我们就是一个人,我们们是一个人,我们也不是一个人,我们也不是一个人,我们也没有一个人,我们就是一个人,我们就是一个人,我们就是一个人,我们就是

SOV/105-59-3-5/27 Switch-off Contactors for High-tension Direct Current Transmission Lines

> arc changes its direction and hence that it may pass through zero. As was shown by experiments, this provides a means of extinguishing the arc in arc-suppression devices of high-tension alternating current contactors, even if the frequency of the oscillations is somewhat higher (500 - 1000 cycles). In this paper a short analysis of the performance of contactors designed on this principle and a description of the experiments carried out with these contactors is given. This model contactor was tested at the rectifier sub-station of the experimental d.c. transmission line from the Kashira water power station to Moscow. Three test series were carried out. Summary: 1) If a high-tension a.c. arc-suppression device is combined with an oscillation circuit, which shunts the arc generated in the arc-suppression device when the contactor disconnects the line, it is possible to create a device which is able to disconnect hightension d.c. transmission lines. 2) If the oscillation circuit is designed correspondingly to the arc characteristic, no previous charging of the oscillation circuit capacity is required. 3) At present air contactors are considered to be the most convenient type, because the contacts remain open after disconnecting. The rest charge on the condenser must be destroyed by a special device which is built-in in the contactor .- There are 6 figures and 5 Soviet

Card 2/3

SCROKIN, F. I.

Metal Cutting

Machining of dovetain profiles. Stan. i instr., 23, No. 6, 1952.

Monthly List of Russian Accessions, Library of Congress November, 1952. UNCLASSIFIED.

SOROKIN, P.I., inzh.

Design of thin-walled elastic rods having open profiles and continuously varying cross sections along the rod. Trudy Kiev. (MIRA 11:5) avt.-dor. inst. no.3:104-116 '57. (MIRA 11:5)

(Blastic rods and wires)

Section is a supplication of the property of t

"On Certain Correlations Between the Geometrical Dimensions of Frame Sections Made of Thin Tubing," by P. I. Sorokin, Krivay Rog Ore Mining Institute, Prikladna Mekhanika, Vol 3, No 2, 1957, pp 179-185

This article considers a symmetrical frame made of channel sections of thin tubing and subjected to antisymmetrical twisting forces. An equation is given which expresses the relationships of certain geometrical dimensions of a frame made up of three joined channel sections, two of which are in the same line, with the third perpendicular to the other two, when the normal torsional-bending stresses are equal at the ends of the tubes.

The equation is solved for the case when the ratio of the height of the channel wall to the flange is greater than or equal to unity and smaller than or equal to four. The flange width is computed for a section of the side frame of the ZIL-50 automobile, and the value obtained was smaller than the width of the flange of the present design.

The formulas given in the article are recommended for use in designing automobile frames and other thin-walled frame structures. (U)

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NEW REPORT OF THE PROPERTY OF

SOROKIN, P.I., inzh.

Calculation of the stability of automobile frames under the action of a symmetrical load and in braking the automobile.

Sbor. nauch. trud. KGRI no.7:273-287 '59. (MIRA 16:9) (Automobiles—Frames)

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SOROKIN, P.I.; POZDNYSHEV, V.M.; POFOV, V.F.; BALINSKIY, V.R.; LESNIKOVICH, S.S.

Casting magnesium iron crankshafts. Lit. proizv. no.5:8-9 My '62. (MIRA 16:3)

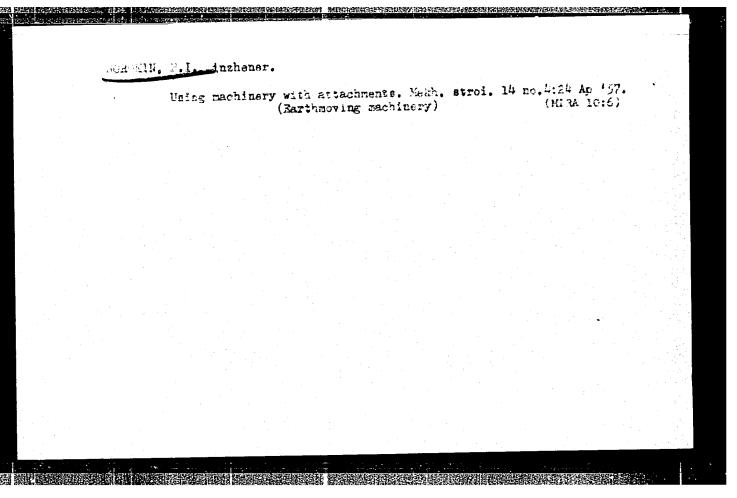
(Cranks and crankshafts) (Iron founding)

FOMINYAH, I.P.; NOVIKOV, P.T.; SCHOKEM, P.T.

Using the primary heat of castings to hasten their annealing.

Lit. proizv. no.4:28-29 Ap '64.

(MIRA 18:7)



SOROKIN, P.I.

Calculation methods in zonal over-all mechanization of the construction of excavated canals by using bulldozers and excavators. Trudy Inst.vod.khoz.i energ. AN Kir.SSR no.5: 49-86 159. (MIRA 13:5)

(Excavating machinery)
(Irrigation canals and flumes)

SOROKIN, P. I., Cand Tech Sci (diss) -- "A method of computing the flow organization of work of zonal complexes of machinery in building canals". Frunze, 1960. 27 pp (Min Agric USSR, Tashkent Inst of Engineers of Irrigation and Mech of Agric TIIIMSKh), 250 copies (KL, No 14, 1960, 134)

SOROKIN, P.1.; KERPICHENKO, M.M., red.; BEYSHENOV, A., tekhn. red.

[Over-all mechanization of earthwork operations in construction]

Kompleksnaia mekhanizateila zemlianykh rabot v stroitel'stre.

Frunze, Kirgizskoe gos.izd-vo, 1960. 58 p. (MIRA 14:6)

(Earthwork—Technological innovations)

SOROKIN, Pavel Il'ich, kand. tekhn. nauk; GANYUSHIN, A.I., red.;
GORYACHKINA, R.A., tekhn. red.

[Manual for a bulldozer operator] Posobie mashinistu bul'dozera. Moskva, Avtotransizdat, 1962. 128 p. (MIRA 15:11)
(Bulldozers)

SOROKIN, P.I., kand.tekhn.nauk

Designing a flow with over-all mechanization in erection of an earth roadbed. Avt. dor, 26 no.2:24-26 f '63. (MIRA 16:4)

(Road construction)

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SOROKIN, P.I.; FOMINYKH, I.P.; BESPALOV, Ya.G.; POBEREZKIN, A.Z.; ZINCHENKO, A.M.; OSKOLKOV, Ye.A.

Inoculation of cupola cast iron with rare-earth metal alloys. Lit. proizv. no.9:27-31 S '64. (MIRA 18:10)

SOROKIN. P.M. (Moscow)

Experience in teaching the topic "Percentage." Mat. v shkole (MIRA 11:7) (Percentage.—Study and teaching)

11/(4)(2)

SOV/92-58-9-21/36

AUTHOR:

Sorokin, P.M., Engineer

TITLE:

Revision of the Flow Scheme of the Gas Fractionating Unit at the Catalytic Cracking Plant (Izmeneniye skhemy gazofraktsioniruyushchey ustanovki kataliticheskogo

krekinga)

PERIODICAL: Neftyanik, 1958, Nr 9, p 22 (USSR)

ABSTRACT: In view of the fact that the gatalytic cracking unit of the Omsk refinery is presently being used for processing heavy crudes, its gas fractionating equipment receives a larger quantity of gas. Therefore, it has been found necessary to revise the flow scheme of gas fractionators as follows: the gas under pressure of 13-14 atm proceeds from the reflux tanks of the stabiliser and isopropane tower directly to gasoline mixing chamber (operating under 10 atm pressure) thus bypassing the absorber to which it would have come according to the original flow scheme. As a result of this measure, the load of absorbers of the gas fractionating unit decreased, and the consumption of steam, water, electric power and of gas used by gas motors dropped.

ASSOCIATION: Omskiy NPZ (The Omsk Refinery) Card 1/1

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11(0)

AUTHOR: Sorokin, P.M., Engineer

sov/92-58-10-18/30

TITLE: Alkylation Unit is Saving Steam (Ekonomiya para na alkiliruyushchey ustanovke)

PERIODICAL: Neftyanik, 1958, Nr 10, p 25 (USSR)

ABSTRACT: One of the processing units of the Omsk refinery is using 30 atm steam to preheat its feed. This condensed steam having approximately 194°C is brought afterwards to the condensation unit where it boils up for the second time due to the drop in pressure. In this way it becomes possible to obtain from the 30 atm condensed steam an additional quantity of exhaust steam. It is brought from the reboiler through the separator to the exhaust steam line and is used for technical purposes.

ASSOCIATION: Omskiy NPZ (The Omsk Refinery)

Card 1/1

SURMANE (in cape); Given Names

Country: Bulgaria

Academic Degrees: not indicated

not indicated

Affiliation:

Source: Sofia, Priroda, No 1, Jan/Feb 61, pp 80-81

"The Analysis of Luminescence in Microbiology."

Data:

CIA-RDP86-00513R001652510011-9 "APPROVED FOR RELEASE: 08/23/2000

SOROKIN, P.P. Amino acid composition of gram-positive and gram-negative bacteria. Ukr. biokhim. zhur. 37 no.2:239-242 165.

l. le erinarnyy institut zaraznykh i parazitarnykh bolezney Bolgarskoy Akademii sel'skokhozyaystvennykh nauk, Sofiya.

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SOROKIN F. P.

Oboridovanie vremennykh peregruzochcykh punktov na morskom poberezhie. Equipment of tempory trans-shirping joints on the sea const. Astrakhan Morskoi transport, 1942. To p. diagna Denovy voenno-morskogo dela).

DLC: TC373.S6

PRUDENTOV, Aleksandr Ivanovich; SOROKIN, P.P., kand.tekhn.nauk, nauchnyy red.; NECHAYEV, G.A., red:izd-va; PUL'KINA, Ye.A., tekhn.red.

[Reinforced concrete tubular sectional piles] Zhelezobetonnye polye sbornye svai. Leningrad, Gos.izd-vo lit-ry po stroit., arkhit. i stroit.materialam, 1959. 109 p. (MIRA 12:10) (Piling (Civil engineering))

GODES, E.G., inzh.; SHASHKOV, S.A., kand. tekhn. nauk; BAUM, V.A., inzh.; SOROKIN, P.P., kand. tekhn. nauk, retsenzent; LISITSYN, B.V., inzh., retsenzent; BESPALOV, I.V., inzh., nauchnyy red.; PENOVA, Ye.M., red. izd-va; VORONETSKAYA, L.V., tekhn. red.

[Reinforcing river banks near factory grounds]Ukreplenie beregov rek na zavodskikh territoriiakh; proizvodstvennyi opyt. Leningrad, Gos. izd-vo lit-ry po stroit., arkhit. i stroit. materialam, 1961. 134 p. (MIRA 14:10)

(Hydraulic engineering)

SOROKIN, P.P., kand. tekhn. nauk; TSUKERMAN, N.Ya., inzh. Prinimal uchastiye PRUDENTOV, A.I., inzh.; KARPOV, V.V., kand. tekhn. nauk, nauchnyy red.; ZHURAVSKIY, N.A., red. izd-va; PUL'KINA, Ye.A., tekhn. red.

[Piling] Svainye raboty. Leningrad, Gos. izd-vo lit-ry po stroit., arkhit. i stroit. materialam, 1961. 213 p. (MIRA 15:3)

(Filing (Civil engineering))

SOROKIN, P.P., kand. tekhn. nauk, nauchn. red.

[Designing and operating plants with straight-flow hydraulic classifiers; for fractionation of sand and gravel mixes] Proektirovanie i ekspluatatsiia ustanovok s priamotochnymi gidroklassifikatorami; dlia fraktsionirovaniia peschanograviinykh smesei. Leningrad, 1962. 151 p.

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1. Vsesoyuznyy nauchno-issledovatel'skiy institut gidro-tekhnicheskikh i sanitarno-tekhnicheskikh rabot.

GARMASH, V.M.; SOROKIN, P.S.

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1. Lebedinskiy rudnik. (Lebedi region (Kursk Magnetic Anomaly)—Mine drainage)

SOROKIN, P.V.

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1949, No 3 s26-30

So: Letonis' No 33, 1949

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The Kama Paper Industry Combine in the fifth and sixth five-year plans. Bum.prom. 31 no.1:25-26 Ja '56. (MLRA 9:5)

1. Nachal'nik planowo-ekonomicheskogo otdela Kamakogo tsellyulovno-bumazhnogo kombinata.

(Kama Valley--Paper industry)

KAMENSKIY, A.V., red.; SOROKIN, P.V., red.; CHEREPANOV, V.A., red.; VERSHININ, T.I., red.izd-va; PASTUKHOV, M.A., tekhn. red.

[Twenty-fifth anniversary of the Kama Woodpulp and Paper Combine] Kamskii tsell'iulozno-bumazhnyi kombinat; 25 let. Perm', Permskoe knizhnoe izd-vo, 1962. 119 p. (MIRA 16:4)

(Krasnokamsk-Woodpulp industry)

SOROKIN, P.V.

Following the road toward the increase of labor productivity. Bum. prom. [38] no.6:19-20 Je 163. (MIRA 16:7)

1. Zamestitel direktora po ekonomika Kamskogo tsellyuloznobumazhnogo kombinata. (Woodpulp industry-labor productivity)

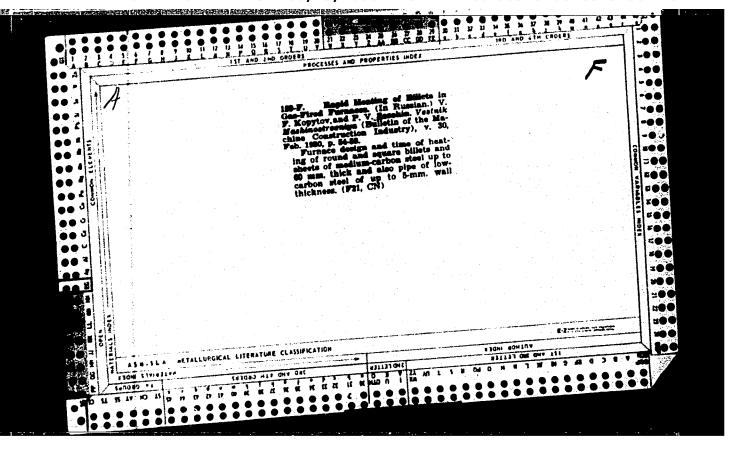
SOROKIN, P. V.

Dopuski na razmery stal'nogo fasonnogo lit'ia. (Vestn. Mash., 1949, no. 7) (Tolerances for dimensions of profile steel castings.)

DLC: TN4,V4

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Nekotorye osobennosti kontrolia razmerov litykh detalei individual'nogo i melkoseriinogo proizvodstva. (Vestn. Mash., 1951, no. 1, p. 77-90)

Includes bibliography.

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DLC: TN4.V4

SG: Manufacturing and Mechanical Engineering in the Soviet Union, Library of Congress, 1953.

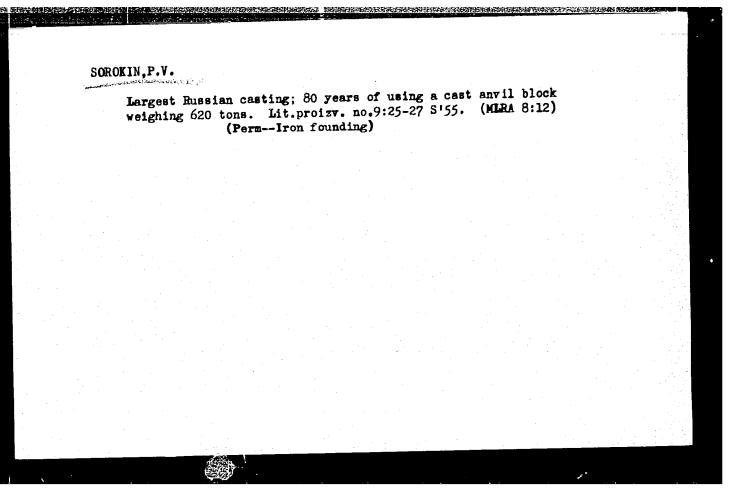
KOPYTOV, V.F., kandidat tekhnicheskikh nauk; SOROKIN, P.V.; POPOVA, S.M., tekhnicheskiy redaktor.

[Rapid heating of steel] Skorostnoi magrev stali. Moskva, Gos. nauchno-tekhn.isd-vo mashinostroitel'noi lit-ry, 1952.21 p. (Nauchno-tekhnicheskaia informatsiia) [Microfilm] (MIRA 9:4) (Steel--Heat treatment)

NEKHRNEZI, Yu.A.; SOROKIN, P.V.

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USSR/Miscella	
	meousmachine construction
Card 1/1	
Authors :	Kopytov, V. F., Cand. in Tech. Sci.; Kopitova, G. F., engineer; and Sorokin, P. V.
Title :	Decarbonizing steel in reverbatory furnaces
Periodical :	Vest. mash. 34/3, 36-40, Mar/1954
Abstract :	The products of burning fuel in a reverbatory furnace at high temperature oxidize steel, producing scales on it, and such oxidation causes oxidation of the carbon in the surface layer of the steel. When the decarbonizing of the surface layer is rapid the decarbonized layer is found under the scale after heating. In order to reduce decarbonization it is necessary during hot processing to heat the steel more rapidly. One Russian reference, dated 1949. Graphs.
Institution :	
Submitted	



SOROKI	M, T.V.	
	A897° High-Strength Pattern Compositions for Precision Casting, Model aye sessay posyshemool prochnosti dila rethnoge lit la. (Russlan.) P. V. Sorokin and E. K. Aleksocyskaja, Liteinoe proizvodite 1850, 160-12, Dec., p. 2-4. Polyethylene and its properties. Use and evaluation of paraffin or corosin wax and their blends or fusions with polyethylene. Graphs, tables. 6 ref.	
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SOROKIN, P. V., Cand. Tech. Sci.; ALEKSEYEVSKAYA, Ye. K. (Eng.);

"The Use of Shell Molds and Fused Quartz in the Production of Investment Castings," Metody polucheniya otlivok pobyshennoy tochnosti (Methods of Making High-Precision Castings), Moscow, Mashgiz, 1958. 140 p.

PURPOSE: This book is intended for engineers and technicians at plants and institutes as well as in research and planning organizations in all branches of the machine-building industry.